



PSMN025-100HS

N-channel 100 V, 24.5 mOhm, standard level MOSFET in LPAK56D using TrenchMOS technology

26 September 2022

Product data sheet

1. General description

Dual standard level N-channel MOSFET in an LPAK56D (Dual Power-SO8) package using TrenchMOS technology.

2. Features and benefits

- High peak drain current I_{DM}
- Copper clip and flexible Leads
- High operating junction temperature $T_j = 175\text{ °C}$
- Superior reliability
- Low body diode reverse recovery charge Q_r

3. Applications

- Synchronous rectifier
- Forward and flyback converter
- Industrial drive
- Power management system
- Uninterruptible Power Supply (UPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2		-	-	29.5	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1		-	-	68	W
T _j	junction temperature			-55	-	175	°C
Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11		-	19.5	24.5	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11 ; Fig. 12		-	54	68	mΩ
Dynamic characteristics FET1 and FET2							
Q _{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; Fig. 13 ; Fig. 14		-	13.1	-	nC
Q _{G(tot)}	total gate charge			-	38.1	-	nC
Avalanche Ruggedness FET1 and FET2							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 29.5 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[1] [2]	-	-	83	mJ

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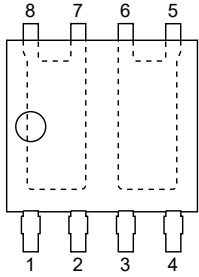
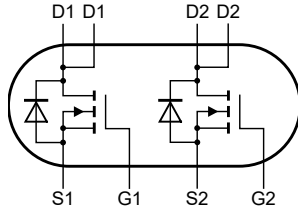
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode FET1 and FET2						
Q_r	recovered charge	$I_S = 5\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	62.2	-	nC

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 <p>LFPAK56D; Dual LPAK (SOT1205)</p>	 <p>mbk725</p>
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN025-100HS	LFPAK56D; Dual LPAK	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN025-100HS	25RS10H

8. Limiting values

Table 5. Limiting values

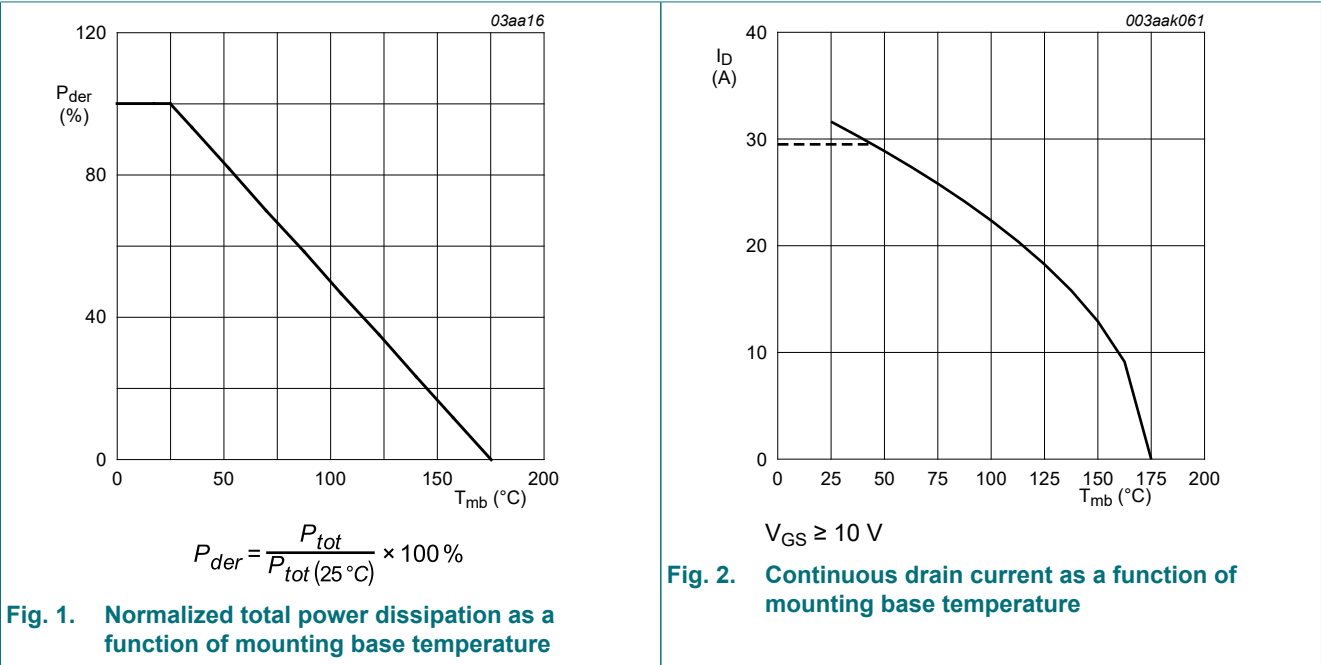
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage	DC; $T_j \leq 175\text{ }^\circ\text{C}$	-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1	-	68	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 2	-	29.5	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ }^\circ\text{C}$; Fig. 2	-	22	A

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Symbol	Parameter	Conditions		Min	Max	Unit
I_{DM}	peak drain current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25\text{ }^{\circ}C$; Fig. 3		-	126	A
T_{stg}	storage temperature			-55	175	$^{\circ}C$
T_j	junction temperature			-55	175	$^{\circ}C$
$T_{sld(M)}$	peak soldering temperature			-	260	$^{\circ}C$
Source-drain diode FET1 and FET2						
I_S	source current	$T_{mb} = 25\text{ }^{\circ}C$		-	29.5	A
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25\text{ }^{\circ}C$		-	126	A
Avalanche Ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 29.5\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ }^{\circ}C$; unclamped; Fig. 4	[1] [2]	-	83	mJ

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



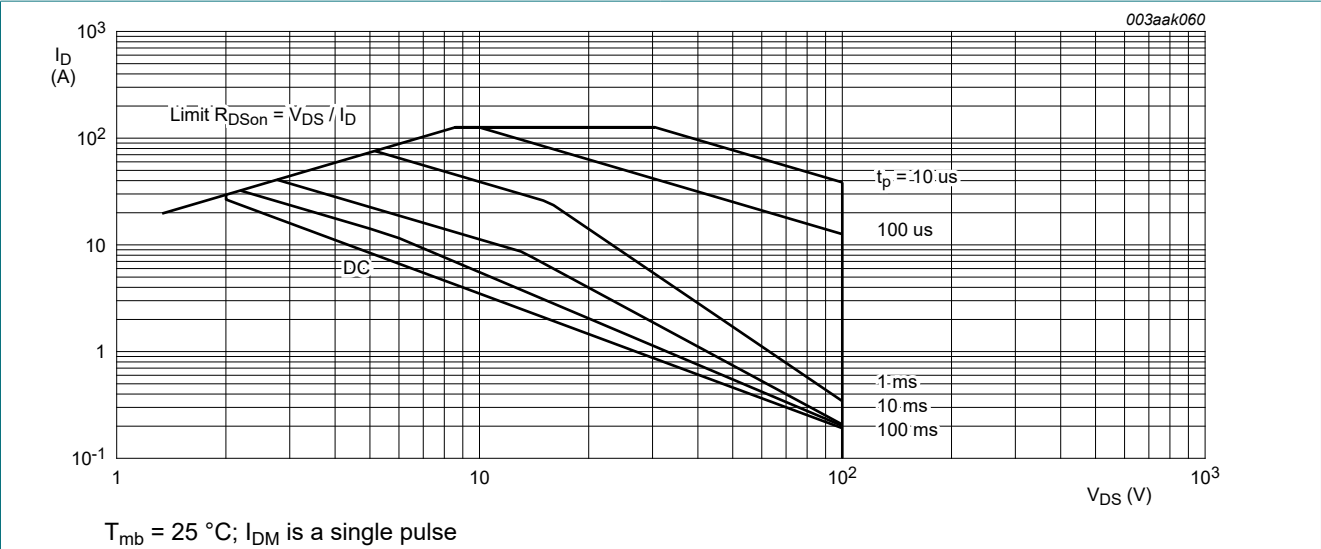


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

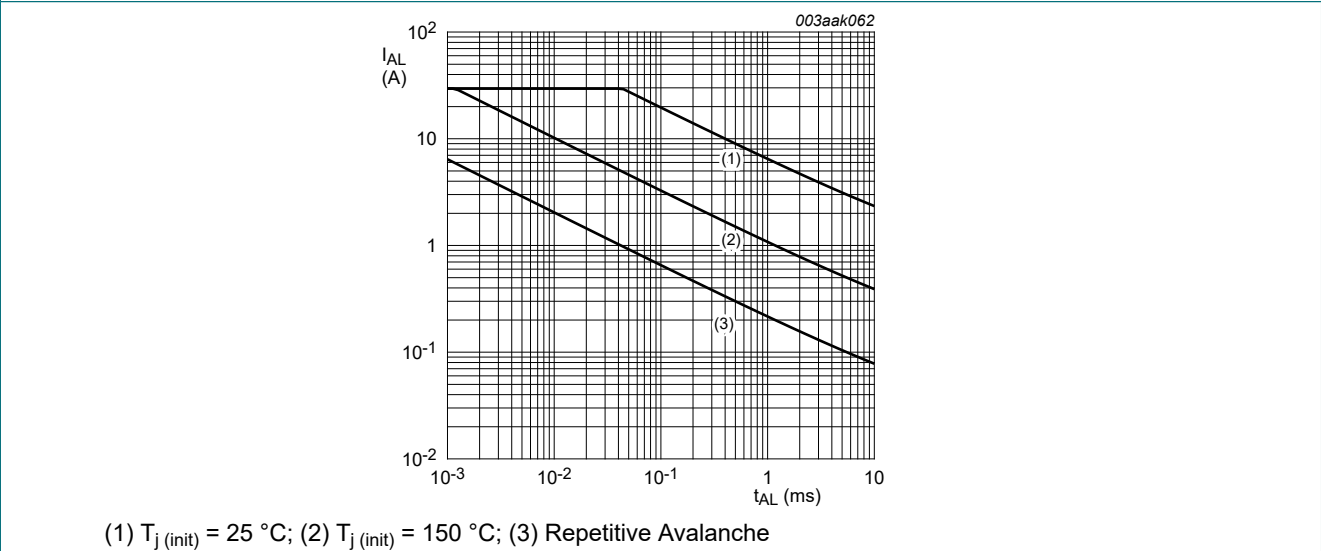


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	2.21	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

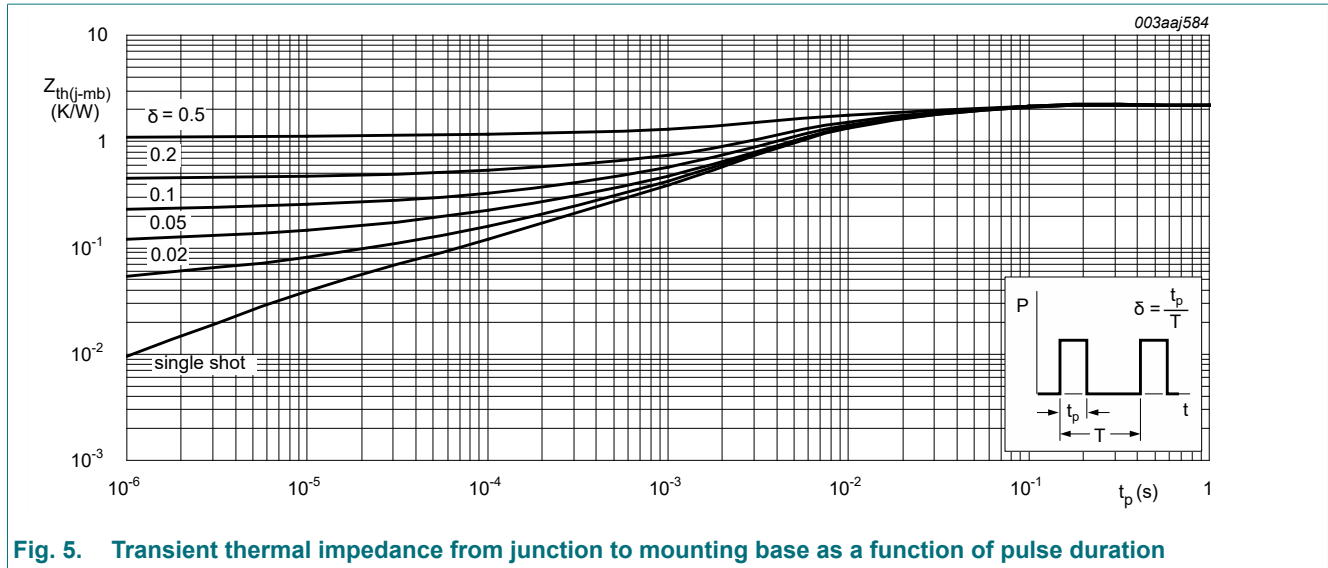


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics FET1 and FET2						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = -55 ^\circ C$	90	-	-	V
		$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA$; $V_{DS} = V_{GS}$; $T_j = 25 ^\circ C$; Fig. 9 ; Fig. 10	2.4	3	4	V
		$I_D = 1 mA$; $V_{DS} = V_{GS}$; $T_j = 175 ^\circ C$; Fig. 10	1	-	-	V
		$I_D = 1 mA$; $V_{DS} = V_{GS}$; $T_j = -55 ^\circ C$; Fig. 10	-	-	4.5	V
I_{DSS}	drain leakage current	$V_{DS} = 100 V$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	-	0.02	1	μA
		$V_{DS} = 100 V$; $V_{GS} = 0 V$; $T_j = 175 ^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	2	100	nA
		$V_{GS} = 20 V$; $V_{DS} = 0 V$; $T_j = 25 ^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V$; $I_D = 10 A$; $T_j = 25 ^\circ C$; Fig. 11	-	19.5	24.5	m Ω
		$V_{GS} = 10 V$; $I_D = 10 A$; $T_j = 175 ^\circ C$; Fig. 11 ; Fig. 12	-	54	68	m Ω
Dynamic characteristics FET1 and FET2						
$Q_{G(tot)}$	total gate charge	$I_D = 5 A$; $V_{DS} = 80 V$; $V_{GS} = 10 V$; $T_j = 25 ^\circ C$; Fig. 13 ; Fig. 14	-	38.1	-	nC
Q_{GS}	gate-source charge		-	5.7	-	nC
Q_{GD}	gate-drain charge		-	13.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 25 V$; $V_{GS} = 0 V$; $f = 1 MHz$; $T_j = 25 ^\circ C$; Fig. 15	-	1827	2436	pF
C_{oss}	output capacitance		-	181	217	pF
C_{rss}	reverse transfer capacitance		-	128	175	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 80 V$; $R_L = 15 \Omega$; $V_{GS} = 10 V$; $R_{G(ext)} = 5 \Omega$; $T_j = 25 ^\circ C$	-	8	-	ns
t_r	rise time		-	13.3	-	ns
$t_{d(off)}$	turn-off delay time		-	28.3	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_f	fall time		-	18	-	ns
Source-drain diode FET1 and FET2						
V_{SD}	source-drain voltage	$I_S = 10\text{ A}$; $V_{GS} = 0\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 16	-	0.78	1.2	V
t_{rr}	reverse recovery time	$I_S = 5\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$;	-	38.4	-	ns
Q_r	recovered charge	$V_{DS} = 50\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$	-	62.2	-	nC

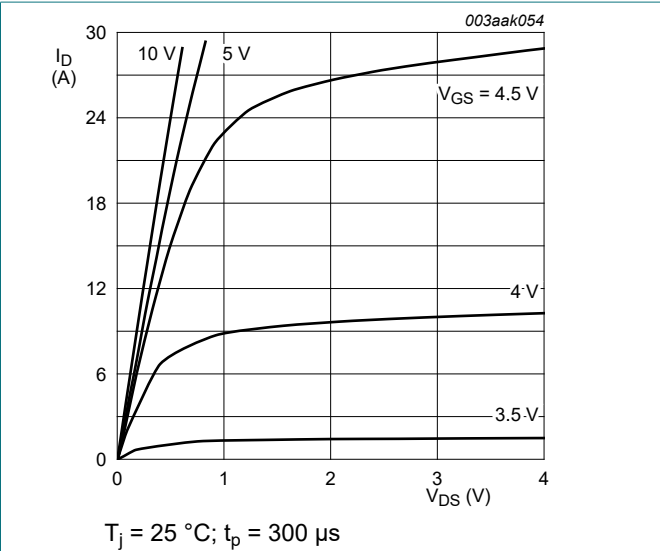


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

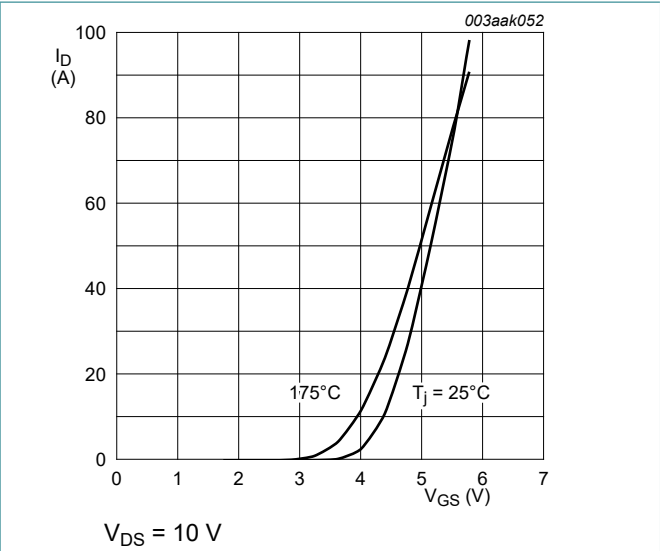


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

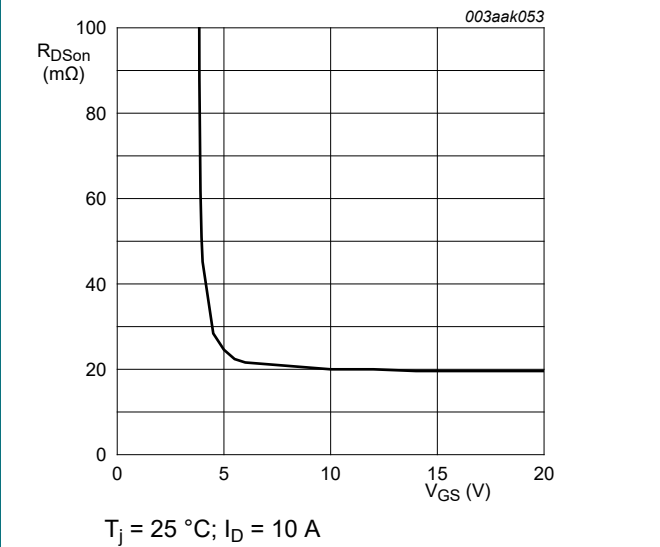


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

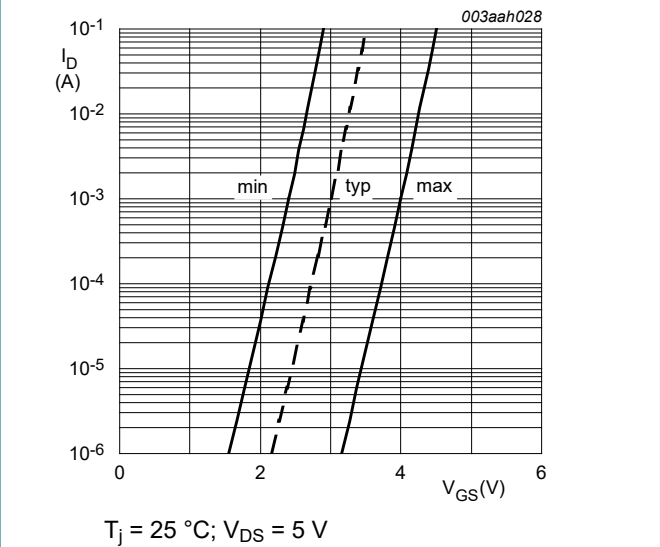


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

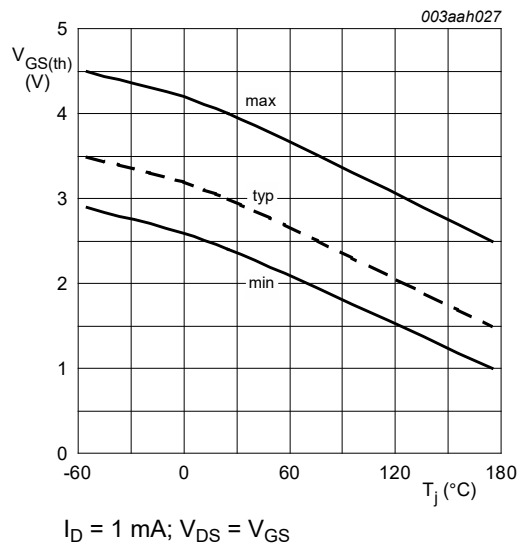


Fig. 10. Gate-source threshold voltage as a function of junction temperature

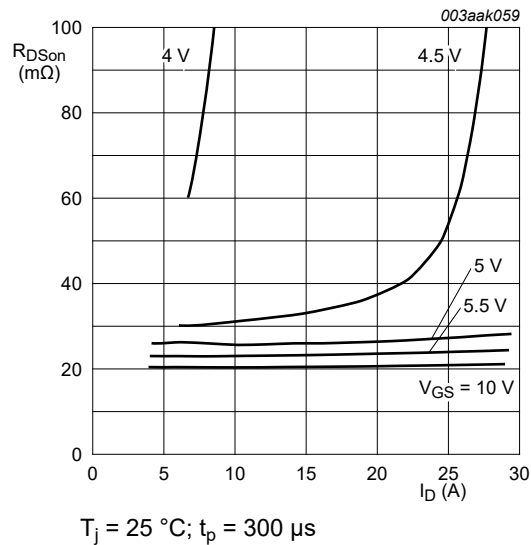


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

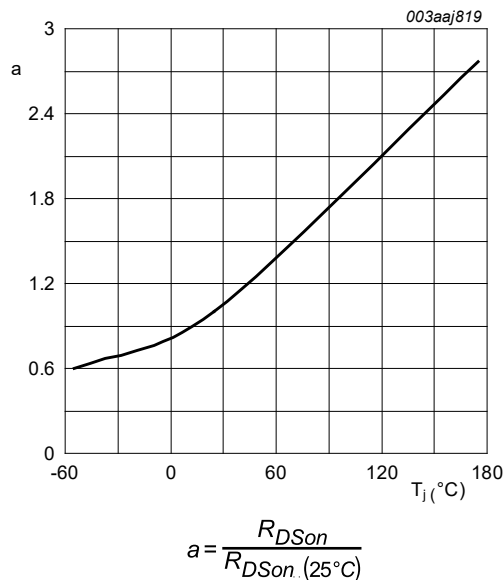


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

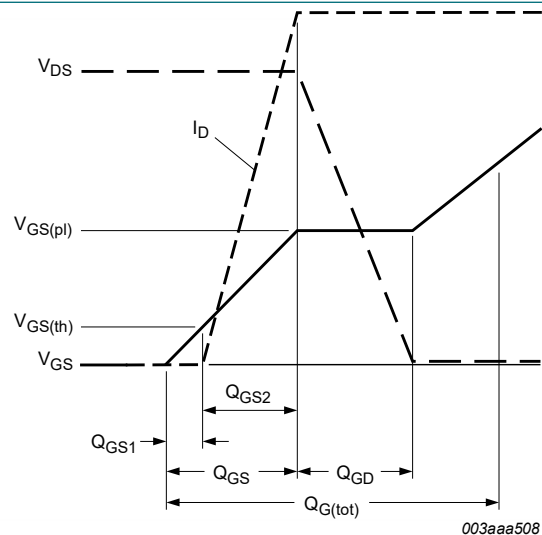


Fig. 13. Gate charge waveform definitions

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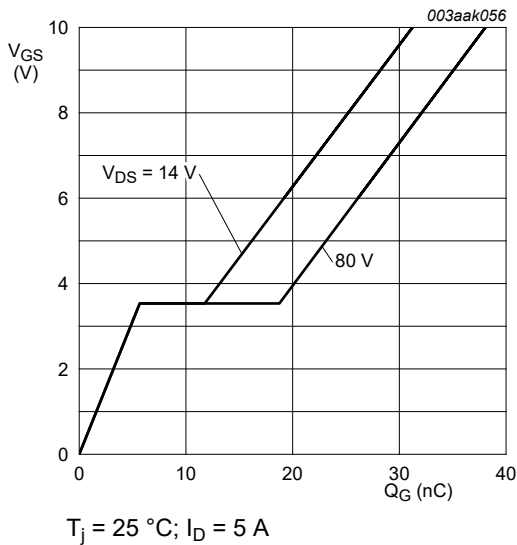


Fig. 14. Gate-source voltage as a function of gate charge; typical values

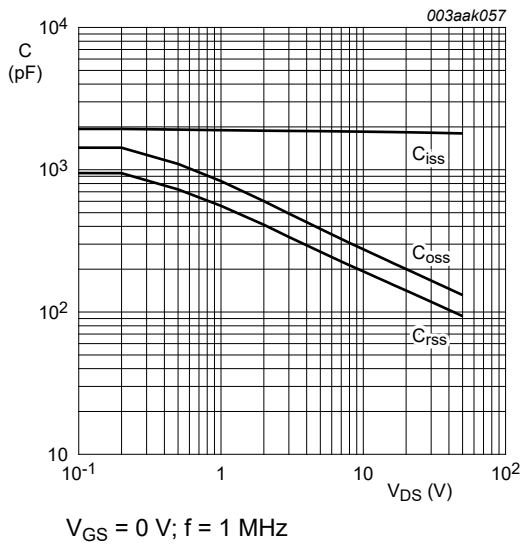


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

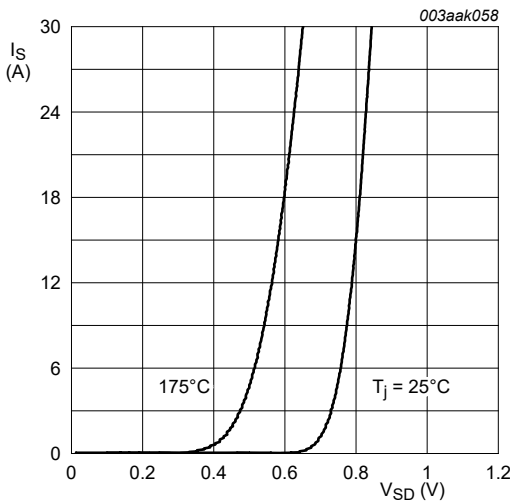


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

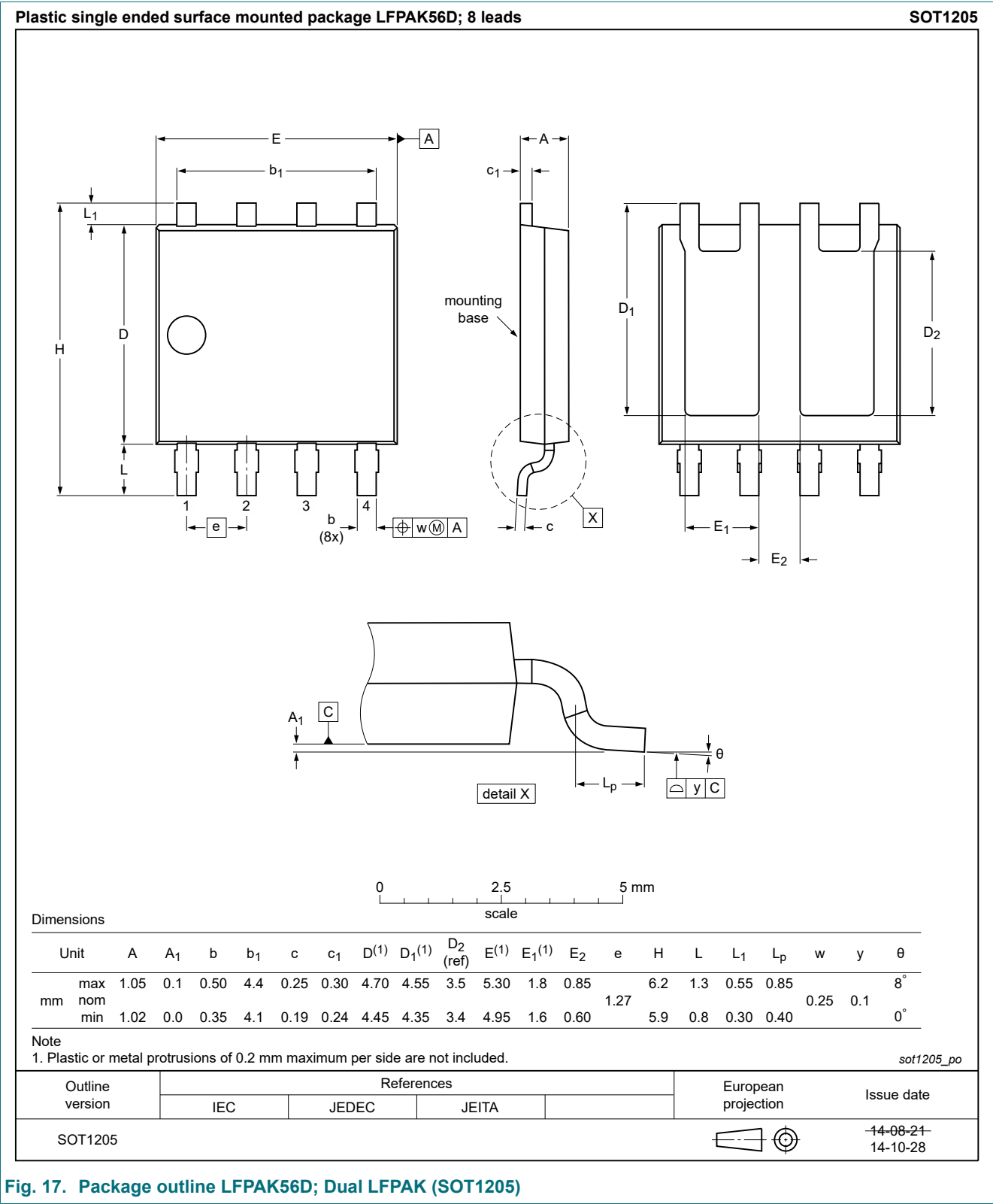


Fig. 17. Package outline LPAK56D; Dual LPAK (SOT1205)

12. Soldering

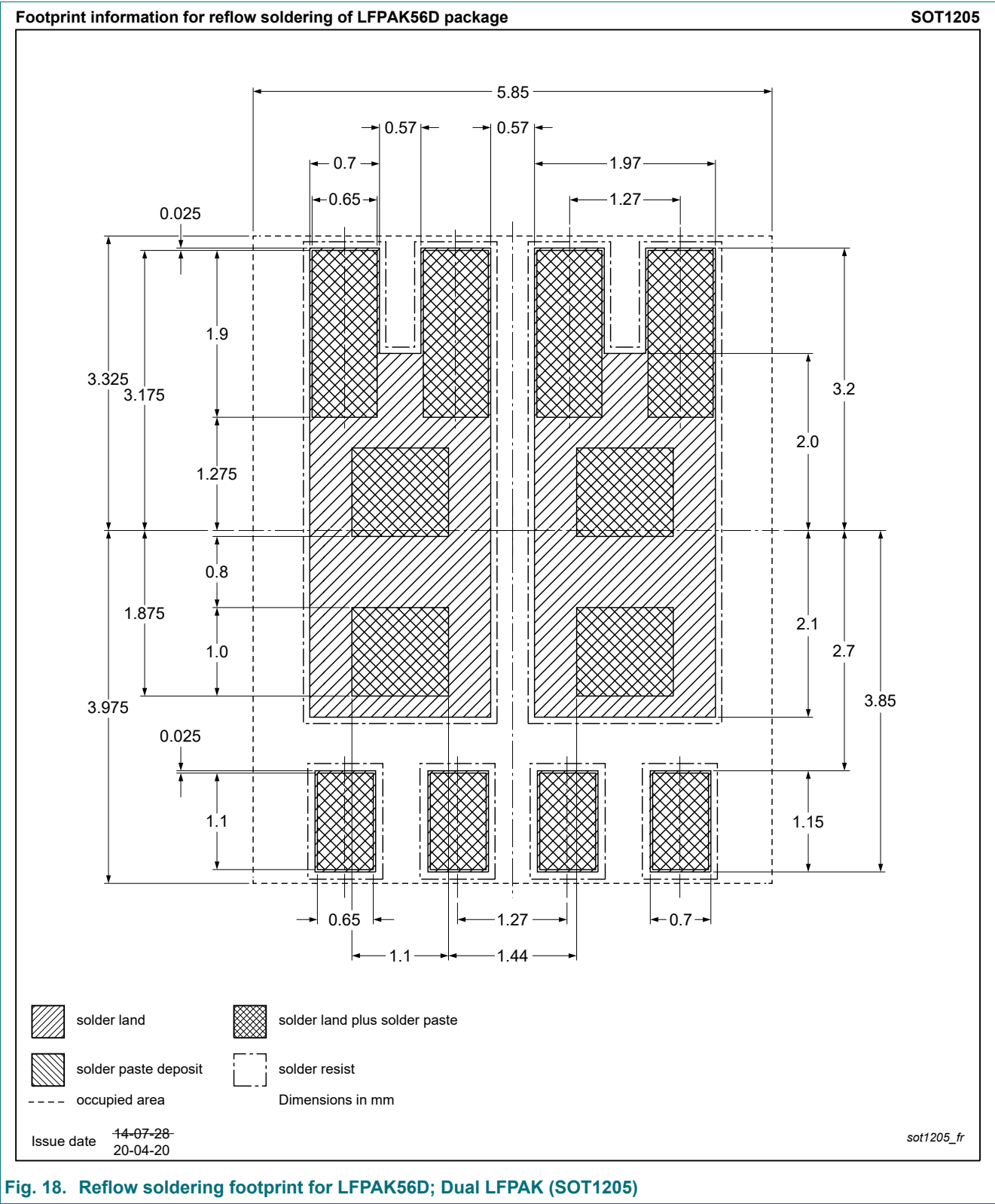


Fig. 18. Reflow soldering footprint for LPAK56D; Dual LPAK (SOT1205)

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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